AMENDMENTS TO THE CLAIMS:

1. (Currently Amended) A liquid crystal display device, comprising:

a display panel including a lower layer at the lowest portion of the display panel and an uppermost layer, positioned above the lowest layer at the uppermost portion of said display panel;

a first substrate forming said uppermost layer of said display panel, including:

a) a switching element on the first substrate

b) a passivation film formed over the whole surface of the first substrate while covering the switching element;

c) a pixel electrode on the passivation film;

d) a black matrix formed on the passivation film and over the switching element;

e) a color filter formed over the pixel electrode; and

f) a first orientation film formed on the black matrix and the color filter and above the pixel electrode;

a second substrate having no switching element disposed thereon, forming said lowest portion of the display panel, said second substrate being [[and]] aligned with the first substrate, both first substrate and said switching element thereon being turned upside down, and said second substrate having a bottom surface thereof formed adjacent to a backlight device, said backlight

device being disposed beneath said second substrate, to prevent the degradation of contrast resulting from the mixing of dispersed light, having a common electrode and a second orientation film, the orientation film formed on the common electrode;

a sealant for sealing the first and second substrates; and

a liquid crystal layer interposed between the first and second substrates.

2. (Previously Presented) The liquid crystal display device of claim 1, wherein the switching element is a thin film transistor, the thin film transistor having a gate electrode formed on the first substrate, a gate insulating layer formed on the exposed surface of the first substrate while covering the gate electrode, a semiconductor layer formed over the gate electrode, a source electrode overlapping one end portion of the semiconductor layer, and a drain electrode overlapping the other end portion of the semiconductor layer.

3. (Original) The liquid crystal display device of claim 2, further comprising a first light absorbing film formed under the gate electrode, a second light absorbing film formed under the source electrode, and a third light absorbing film formed under the drain electrode.

4. (Original) The liquid crystal display device of claim 2, further comprising, a first light absorbing film formed under the gate electrode and a second light absorbing film formed under the semiconductor layer.

5. (Original) The liquid crystal display device of claim 3, further comprising, a gate line connected with the gate electrode and a data line connected with the source electrode, the first light absorbing film formed under the gate line, the second light absorbing film formed under data line.

6. (Original) The liquid crystal display device of claim 4, further comprising, a gate line connected with the gate electrode and a data line connected with the source electrode, the first light absorbing film formed under the gate line, the second light absorbing film formed under data line.

7. (Previously Presented) The liquid crystal display device of claim 5, wherein the back light device is for supplying light to the liquid crystal layer.

8. (Original) The liquid crystal display device of claim 7, wherein the common electrode and the pixel electrode are made of indium tin oxide (ITO).

9. (Original) The liquid crystal display device of claim 1, wherein the common electrode is made of an opaque conductive material.

10. (Original) The liquid crystal display device of claim 3, wherein the common electrode is made of an opaque conductive material.

11. (Original) The liquid crystal display device of claim 4, wherein the common electrode is made of an opaque conductive material.

12. (Previously Presented) A method of manufacturing a liquid crystal display device which comprises an array of thin film transistors and an array of pixel electrodes including:

forming a gate line and a gate electrode on a first substrate said first substrate forming the uppermost layer of a display panel, the gate electrode extending from the gate line;

forming a gate insulating layer on the exposed surface of the upper substrate while covering the gate line and the gate electrode;

forming a semiconductor layer over the gate electrode;

forming a data line and source and drain electrodes, the source electrode overlapping one end portion of the semiconductor layer, the drain electrode overlapping the other end portion of the semiconductor layer, the

source and drain electrodes spaced apart from each other, the source electrode extending from the data line, said gate, source and drain electrodes comprising a thin film transistor formed on said first substrate;

forming a passivation film over the whole surface of the first substrate while covering the source and drain electrodes, the passivation film having a contact hole on the drain electrode;

forming a pixel electrode on the passivation film, the pixel electrode electrically connected with the drain electrode through the contact hole;

forming a color filter on the pixel electrode;

forming a black matrix over the thin film transistor;

forming a first orientation film on the color filters and the black matrices;

forming a common electrode on a second substrate;

forming a second orientation film on the common electrode;

aligning the first substrate turned upside down with the second substrate so that the thin film transistor is also turned upside down and the first orientation film of the first substrate is opposite to the second orientation film of the second substrate with a gap therebetween to prevent degradation of the contact resulting from the mixing of dispersed light;

sealing the first and second substrates with a sealant; and

injecting a liquid crystal between the first substrate and the second substrate.

13. (Previously Presented) The method of claim 12, further comprising:

forming a first light absorbing film between the first substrate and the gate electrode; and

forming a second light absorbing film between the semiconductor layer and the source and drain electrodes.

14. (Previously Presented) The method of claim 12, further comprising:

forming a first light absorbing film between the first substrate and the gate electrode; and

forming a second light absorbing film between the semiconductor layer and the gate insulating layer.

15. (Original) The method of claim 13, wherein the common electrode and the pixel electrode are made of indium tin oxide.

16. (Original) The method of claim 14, wherein the common electrode and the pixel electrode are made of indium tin oxide.

17. (Original) The method of claim 13, wherein the common electrode is made of an opaque conductive material.

18. (Original) The method of claim 14, wherein the common electrode is made of an opaque conductive material.